

IN THE ABSTRACT OF THE DISCLOSURE:

Please amend the abstract as follows:

ABSTRACT OF THE DISCLOSURE

~~Provided is~~ In a technique ~~making it possible~~ to improve the high-frequency power gain of an LDMOS. ~~The~~, the distance from the surface of a passivation film covering electrode pads to the rear surface of a silicon substrate is set into 200 μm or less, or a trench of 2 μm or more in thickness, in which an insulating film or a conductor is embedded, is ~~made~~ formed between a region where a p type impurity is diffused, when a p⁺ type source penetrating layer is formed, and the channel region of a third LDMOS, so as to extend from the front surface of a semiconductor layer toward a silicon substrate. This trench restrains the p⁺ type source penetrating layer from spreading to the channel region, thereby lowering the inductance or the resistance of the source and improving the high-frequency power gain.